

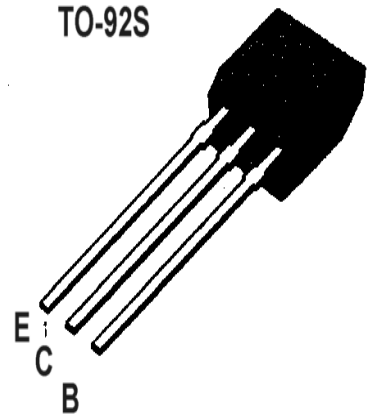
**PNP Transistors**

—PNP Silicon—

■■ **APPLICATION:** Audio Low Frequency Power Amplifier Applications.

■■ **MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V <sub>CBO</sub>	-35	V
Collector-emitter voltage	V <sub>CEO</sub>	-30	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-0.5	A
Collector Power Dissipation	P <sub>C</sub>	0.3	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55~150	°C



■■ **ELECTRICAL CHARACTERISTICS** (Ta=25°C, R<sub>G</sub>=10Ω)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-35			V	I <sub>C</sub> =-20uA	I <sub>E</sub> =0	
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-30			V	I <sub>C</sub> =-1mA	I <sub>B</sub> =0	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5			V	I <sub>E</sub> =-20uA	I <sub>C</sub> =0	
Collector Cut-off Current	I <sub>CBO</sub>			-0.1	uA	V <sub>CB</sub> =-35V	I <sub>E</sub> =0	
Emitter Cut-off Current	I <sub>EBO</sub>			-0.1	uA	V <sub>EB</sub> =-3V	I <sub>C</sub> =0	
Base-Emitter Voltage	V <sub>BE</sub>		-0.8	-1	V	V <sub>CE</sub> =-1V	I <sub>C</sub> =-0.1A	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			-0.25	V	I <sub>C</sub> =-0.1A	I <sub>B</sub> =-10mA	
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>			-1	V	I <sub>C</sub> =-0.1A	I <sub>B</sub> =-10mA	
DC Current Gain	H <sub>FE</sub>	70		400	β	V <sub>CE</sub> =-1V	I <sub>C</sub> =-0.1A	
Gain bandwidth product	f <sub>T</sub>	80			MHz	V <sub>CE</sub> =-10V	I <sub>C</sub> =-1mA	
Common Base Output Capacitance	C <sub>ob</sub>		4	7	pF	V <sub>CB</sub> =-10V	I <sub>E</sub> =0	f=1MHz

■■ **H<sub>FE</sub> Classification And Marking**

Print Mark	A562		
Classification	O	Y	GR
H <sub>FE</sub>	70~140	120~240	200~400